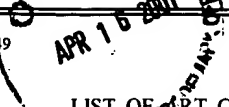


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<div style="text-align: center;"> <b>LIST OF ART CITED BY APPLICANT</b>          (Use several sheets if necessary)       </div>				APPLICANT Ammar Derraa				
				FILING DATE November 13, 2000		GROUP 2812		
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
5	AA	4,957,881	09/90	Crotti	X	X		
5	AB	5,157,002	10/92	Moon				
5	AC	5,421,958	06/95	Fathauer et al.				
5	AD	5,427,648	06/95	Pamulapati et al.				
5	AE	5,430,300	07/95	Yue et al.				
5	AF	5,518,950	05/96	Ibok et al.				
5	AG	5,608,285	03/97	Vickers et al.				
5	AH	5,616,519	04/97	Ping				
5	AI	5,627,382	05/97	Canham et al.				
5	AJ	5,665,657	09/97	Lee				
5	AK	5,705,028	01/98	Matsumoto				
5	AL	5,731,214	03/98	Kurihara				
FOREIGN PATENT DOCUMENTS								
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							Yes	No
	AM							
	AN							
	AO							
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5	AP		Boswell, E. et al., "Characterization of Porous Silicon Field Emitter Properties", J.Vac.Sci. Technol. B 14(3), May/June 1996, pp. 1895-1898.					
1	AQ		Sugino, T. et al., "Electron Emission from Boron Nitride Coated Si Field Emitters", Appl. Phys. Lett. 71(18), Nov. 3, 1997, pp. 2704-2706.					
5	AR		Ko, Y. et al., "Electron Emission and Structure Properties of Cesium Carbon Films Prepared by Negative Carbon Ion Beam", J.Appl. Phys. 82(5), Sept. 1, 1997, pp. 2631-2635.					
5	AS		Lee, J. et al., "Emission Characteristics of Silicon Field Emitter Arrays Fabricated by Spin-On-Glass Etch-back Process", 9 <sup>th</sup> Internatl. Vacuum Microelectronics Conference, St. Petersburg 1996, pp. 380-383.					
EXAMINER <i>S. Merer</i>				DATE CONSIDERED <i>1-14-03</i>				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

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				FILING DATE November 13, 2000	GROUP 2812			
U.S. PATENT DOCUMENTS								
Examiner Initial	Class	Document Number	Date	Name	Subclass	Filing Date If Appropriate		
S		AA 3,814,968	06/74	Nathanson et al.	X			
S		AB 5,817,201	10/98	Greschner et al.				
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S		AD 5,141,460	08/92	Jaskie et al.				
S		AE 5,129,850	07/92	Kane et al.				
		AF						
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		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
S	AR		Takai, M. et al., "Enhanced Electron Emission from n-type Porous Si Field Emitter Arrays", Appl. Phys. Lett. 66(4), Jan. 23, 1995, pp. 422-423.					
S	AS		Lee, J. et al., "Fabrication and Characterization of Silicon Field Emitter Arrays by Spin-On-Glass Etch-back Process", J.Vac. Sci. Technol. B 16(1), Jan/Feb. 1998, pp. 238-241.					
~	AT		Matsuura, M. et al., "A Highly Reliable Self-Planarizing Low-k Intermetal Dielectric for Sub-quarter Micron Interconnects", IEEE 1997, pp. 31.6.1 - 31.6.4.					
EXAMINER <div style="text-align: center;">S. meia</div>				DATE CONSIDERED <div style="text-align: center;">1-14-03</div>				
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<b>U.S. PATENT DOCUMENTS</b>								
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<b>FOREIGN PATENT DOCUMENTS</b>								
	Document Number	Date	Country	Class	Subclass	Translation		
						Yes	No	
	AM							
	AN							
	AO							
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	AQ							
<b>OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)</b>								
~	AR		ARTICLE: McClatchie, S. et al., "Low Dielectric Constant Flowfill® Technology for IMD Applications", Electrotech Ltd., Bristol, U.K.,					
			undated, 7 pages, <i>Date unknown</i>					
~	AS		ARTICLE: Kiermasz, A. et al., Electrotech Ltd., U.K., "Planarisation for Sub-Micron Devices Utilising a New Chemistry", presented at					
			DUMIC Conference, California, Feb. 1995, 2 pages.					
~	AT		ARTICLE: Beekmann, K. et al., Electrotech Ltd., U.K., "Sub-Micron Gap Fill and In-Situ Planarisation Using Flowfill™ Technology",					
			presented at ULSI Conference, Portland, OR, October 1995, pp. 1-7.					
EXAMINER <i>G. Meier</i>				DATE CONSIDERED <i>1-14-03</i>				
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